

LMX2487E 7.5 GHz High Performance Delta-Sigma Low Power Dual PLLatinum™ Frequency Synthesizers with 3.0 GHz Integer PLL

General Description

The LMX2487E is a low power, high performance delta-sigma fractional-N PLL with an auxiliary integer-N PLL. It is fabricated using National Semiconductor's advanced process.

With delta-sigma architecture, fractional spurs at lower offset frequencies are pushed to higher frequencies outside the loop bandwidth. The ability to push close in spur and phase noise energy to higher frequencies is a direct function of the modulator order. Unlike analog compensation, the digital feedback technique used in the LMX2487E is highly resistant to changes in temperature and variations in wafer processing. The LMX2487E delta-sigma modulator is programmable up to fourth order, which allows the designer to select the optimum modulator order to fit the phase noise, spur, and lock time requirements of the system.

Serial data for programming the LMX2487E is transferred via a three line high speed (20 MHz) MICROWIRE interface. The LMX2487E offers fine frequency resolution, low spurs, fast programming speed, and a single word write to change the frequency. This makes it ideal for direct digital modulation applications, where the N counter is directly modulated with information. The LMX2487E is available in a 24 lead 4.0 X 4.0 X 0.8 mm LLP package.

Applications

- Cellular phones and base stations
- Direct digital modulation applications
- Satellite and cable TV tuners

- WLAN Standards
- Features

Quadruple Modulus Prescalers for Lower Divide Ratios

- **RF PLL:** 16/17/20/21 or 32/33/36/37
- IF PLL: 8/9 or 16/17

Advanced Delta Sigma Fractional Compensation

- 12 bit or 22 bit selectable fractional modulus
- Up to 4th order programmable delta-sigma modulator

Features for Improved Lock Times and Programming

- Fastlock / Cycle slip reduction
- Integrated time-out counter
- Single word write to change frequencies with Fastlock

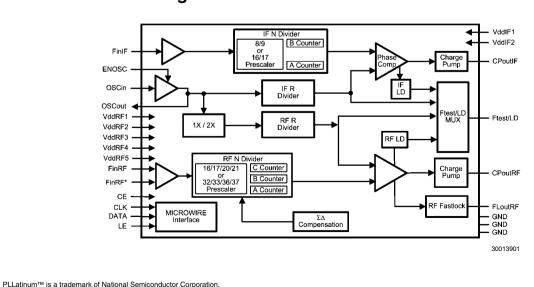
Wide Operating Range

LMX2487E RF PLL: 3.0 GHz to 7.5 GHz

Useful Features

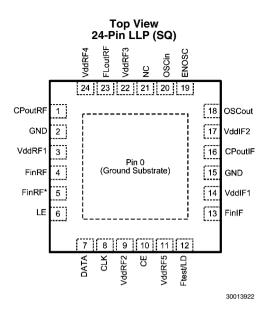
- Digital lock detect output
- Hardware and software power-down control
- On-chip crystal reference frequency doubler.
- RF phase comparison frequency up to 50 MHz
- 2.5 to 3.6 volt operation with I_{CC} = 8.5 mA at 3.0 V





MX2487E High Performance Delta-Sigma Low Power Dual PLLatinum Frequency Synthesize

Connection Diagram



Pin Descriptions

Pin #	Pin Name	I/O	Pin Description
0	GND	-	Ground Substrate. This is on the bottom of the package and must be grounded.
1	CPoutRF	0	RF PLL charge pump output.
2	GND	-	RF PLL analog ground.
3	VddRF1	-	RF PLL analog power supply.
4	FinRF	I	RF PLL high frequency input pin.
5	FinRF*	I	RF PLL complementary high frequency input pin. Shunt to ground with a 100 pF capacitor.
6	LE	I	MICROWIRE Load Enable. High impedance CMOS input. Data stored in the shift registers is loaded into the internal latches when LE goes HIGH
7	DATA	I	MICROWIRE Data. High impedance binary serial data input.
8	CLK	I	MICROWIRE Clock. High impedance CMOS Clock input. Data for the various counters is
			clocked into the 24 bit shift register on the rising edge
9	VddRF2	-	Power supply for RF PLL digital circuitry.
10	CE	I	Chip Enable control pin. Must be pulled high for normal operation.
11	VddRF5	I	Power supply for RF PLL digital circuitry.
12	Ftest/LD	0	Test frequency output / Lock Detect.
13	FinIF	I	IF PLL high frequency input pin.
14	VddIF1	-	IF PLL analog power supply.
15	GND	-	IF PLL digital ground.
16	CPoutIF	0	IF PLL charge pump output
17	VddIF2	-	IF PLL power supply.
18	OSCout	0	Buffered output of the OSCin signal.
19	ENOSC	Ι	Oscillator enable. When this is set to high, the OSCout pin is enabled regardless of the state of other pins or register bits.
20	OSCin	I	Reference Input.
21	NC	I	This pin must be left open.
22	VddRF3	-	Power supply for RF PLL digital circuitry.
23	FLoutRF	0	RF PLL Fastlock Output. Also functions as Programmable TRI-STATE CMOS output.
24	VddRF4	-	RF PLL analog power supply.

Absolute Maximum Ratings (Notes 1, 2)

Parameter	Symbol		Units		
Faranieler	Symbol	Min	Тур	Max	Onits
Power Supply Voltage	V _{CC}	-0.3		4.25	V
Voltage on any pin with GND = 0V	V _i	-0.3		V _{CC} +0.3	V
Storage Temperature Range	T _s	-65		+150	°C
Lead Temperature (Solder 4 sec.)	TL			+260	°C

Recommended Operating Conditions

Parameter	Symbol		Value		Units	
Parameter	Symbol	Min	Тур	Max	Units	
Power Supply Voltage (Note 1)	V _{cc}	2.5	3.0	3.6	V	
Operating Temperature	T _A	-40	25	+85	°C	

Note 1: "Absolute Maximum Ratings" indicate limits beyond which damage to the device may occur. "Recommended Operating Conditions" indicate conditions for which the device is intended to be functional, but do not guarantee specific performance limits. For guaranteed specifications and test conditions, see the Electrical Characteristics. The guaranteed specifications apply only for the test conditions listed. The voltage at all the power supply pins of VddRF1, VddRF2, VddRF3, VddRF4, VddRF5, VddIF1 and VddIF2 must be the same. V_{CC} will be used to refer to the voltage at these pins and I_{CC} will be used to refer to the sum of all currents through all these power pins.

Note 2: This Device is a high performance RF integrated circuit with an ESD rating < 2 kV and is ESD sensitive. Handling and assembly of this device should only be done at ESD-free workstations.

Electrical Characteristics ($V_{CC} = 3.0V$; -40°C $\leq T_A \leq +85°$ C unless otherwise specified)

Cumbal	Parameter		Conditions		Value			
Symbol	Paran	neter	Conditions	Min	Тур	Max	Units	
ICC PARAMETE	RS			•	• •			
I _{CC} RF	Power Supply Current, RF Synthesizer		IF PLL OFF RF PLL ON Charge Pump TRI-STATE		5.7		mA	
I _{cc} IF	Power Supply Current, IF Synthesizer		IF PLL ON RF PLL OFF Charge Pump TRI-STATE		2.5		mA	
I _{CC} TOTAL	Power Supply Current, Entire Synthesizer		IF PLL ON RF PLL ON Charge Pump TRI-STATE		8.5		mA	
I _{CC} PD	Power Down Current		CE = ENOSC = 0V CLK, DATA, LE = 0V		< 1		μA	
RF SYNTHESIZ	ER PARAMET	ERS						
4	Operating Frequency	LMX2487	RF_P = 16	3000		4000	MHz	
f _{FinRF}		y E	RF_P = 32	3000		7500		
P _{FinRF}	Input Sensitiv	vity	3-6 GHz	-10		0	dBm	
			6-7.5 GHz	-5		5	<u> </u>	
f _{COMP}	Phase Detector Frequency (Note 3)					50	MHz	
			$RF_CPG = 0$ $V_{CPoutRF} = V_{CC}/2$		95		μA	
I _{CPoutRF} SRCE	RF Charge P Current	ump Source	$RF_CPG = 1$ $V_{CPoutRF} = V_{CC}/2$		190		μΑ	
	(Note 4)						μA	
			$RF_CPG = 15$ $V_{CPoutRF} = V_{CC}/2$		1520		μA	

Symbol	Devenueter	Conditions		Value		
Symbol	Parameter	Conditions	Min	Тур	Max	Units
		$RF_CPG = 0$ $V_{CPoutRF} = V_{CC}/2$		-95		μA
ISINK	RF Charge Pump Sink	RF_CPG = 1		-190		μA
I _{CPoutRF} SINK	Current (Note 4)	$V_{CPoutRF} = V_{CC}/2$				
		 RF_CPG = 15 V _{CPoutRF} = V _{CC} /2		-1520		μA μA
I _{CPoutRF} TRI	RF Charge Pump TRI- STATE Current Magnitude	$0.5 \le V_{CPoutRF} \le V_{CC}$ -0.5		2	10	nA
I _{CPoutBF} %MIS	Magnitude of RF CP Sink	$V_{CPoutRF} = V_{CC}/2$ RF_CPG > 2		3	10	%
CPoutRF / MIC 1	vs. CP Source Mismatch	$T_A = 25^{\circ}C$ RF_CPG ≤ 2		3	13	%
∣I _{CPoutRF} %V∣	Magnitude of RF CP Current vs. CP Voltage	$0.5 \le V_{CPoutRF} \le V_{CC}$ -0.5 $T_A = 25^{\circ}C$		2	8	%
∣I _{CPoutRF} %T∣	Magnitude of RF CP Current vs. Temperature	$V_{CPoutRF} = V_{CC}/2$		4		%
IF SYNTHESIZE	R PARAMETERS	-				
f _{FinIF}	Operating Frequency	IF_P = 8 IF_P = 16	250 250	_	2000 3000	MHz
p _{FinIF}	IF Input Sensitivity	IF_F = 10	-10		+5	dBm
f _{COMP}	Phase Detector Frequency				10	MHz
I _{CPoutIF} SRCE	IF Charge Pump Source Current	$V_{CPoutIF} = V_{CC}/2$		3.5		mA
I _{CPoutIF} SINK	IF Charge Pump Sink Current	$V_{CPoutIF} = V_{CC}/2$		-3.5		mA
I _{CPoutIF} TRI	IF Charge Pump TRI- STATE Current Magnitude	$0.5 \le V_{CPoutlF} \le V_{CC} RF - 0.5$		2	10	nA
I _{CPoutIF} %MIS	Magnitude of IF CP Sink vs. CP Source Mismatch			1	8	%
I _{CPoutIF} %V	Magnitude of IF CP Current vs. CP Voltage	$0.5 \le V_{CPout F} \le V_{CC}$ -0.5 T _A = 25°C		4	10	%
I I _{CPoutIF} %TEMP	Magnitude of IF CP Current vs. Temperature	$V_{CPoutIF} = V_{CC}/2$		4		%
OSCILLATOR P	ARAMETERS			••••••		
f	Oscillator Operating	OSC2X = 0	5		110	MHz
f _{OSCin}	Frequency	OSC2X = 1	5		20	MHz
V _{OSCin}	Oscillator Input Sensitivity		0.5		V_{CC}	V _{P-P}
I _{OSCin}	Oscillator Input Current		-100		100	μA
SPURS				· · ·		
	Spurs in band(Note 5)			-55		dBc

Or which a l	Demonster	O an althion o	Value				
Symbol	Parameter	Conditions Min		Тур	Max	- Units	
PHASE NOISE							
L _{F1Hz} RF		RF_CPG = 0		-202			
	RF Synthesizer	RF_CPG = 1		-204			
	Normalized Phase Noise	RF_CPG = 3		-206		dBc/Hz	
	Contribution(Note 6)	RF_CPG = 7		-210			
		RF_CPG = 15		-210			
L _{F1Hz} IF	IF Synthesizer Normalized Phase Noise Contribution			-209		dBc/Hz	
DIGITAL INTER	RFACE (DATA, CLK, LE, EN	IOSC, CE, Ftest/LD, FLoutRF)		·			
V _{IH}	High-Level Input Voltage		1.6		V _{CC}	V	
V _{IL}	Low-Level Input Voltage				0.4	V	
I _{IH}	High-Level Input Current	$V_{IH} = V_{CC}$	-1.0		1.0	μA	
I _{IL}	Low-Level Input Current	$V_{IL} = 0 V$	-1.0		1.0	μA	
V _{OH}	High-Level Output Voltage	I _{OH} = -500 μA	V _{CC} -0.4			v	
V _{OL}	Low-Level Output Voltage	I _{OL} = 500 μA			0.4	v	
MICROWIRE IN	NTERFACE TIMING		•			•	
t _{cs}	Data to Clock Set Up Time	See MICROWIRE Input Timing	25			ns	
t _{CH}	Data to Clock Hold Time	See MICROWIRE Input Timing	8			ns	
t _{сwн}	Clock Pulse Width High	See MICROWIRE Input Timing	25			ns	
t _{CWL}	Clock Pulse Width Low	See MICROWIRE Input Timing	25			ns	
t _{ES}	Clock to Load Enable Set Up Time	See MICROWIRE Input Timing	25			ns	
t _{EW}	Load Enable Pulse Width	See MICROWIRE Input Timing	25			ns	

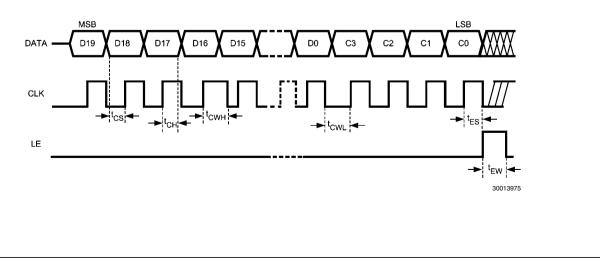
Note 3: For Phase Detector Frequencies above 20 MHz, Cycle Slip Reduction (CSR) may be required. Legal divide ratios are also required.

Note 4: Refer to table in Section 2.4.2 RF_CPG -- RF PLL Charge Pump Gain for complete listing of charge pump currents.

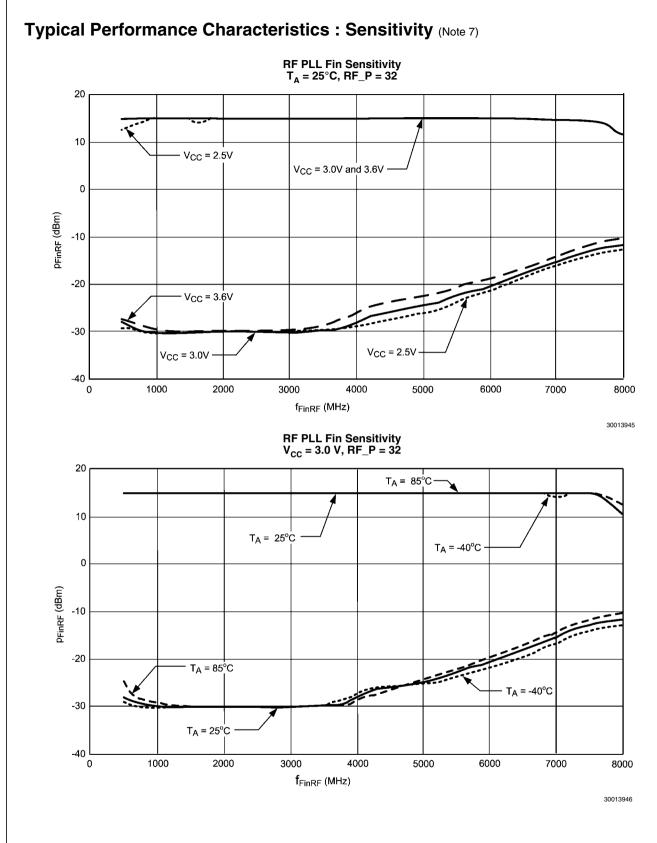
Note 5: In order to measure the in-band spur, the fractional word is chosen such that when reduced to lowest terms, the fractional numerator is one. The spur offset frequency is chosen to be the comparison frequency divided by the reduced fractional denominator. The loop bandwidth must be sufficiently wide to negate the impact of the loop filter. Measurement conditions are: Spur Offset Frequency = 10 kHz, Loop Bandwidth = 100 kHz, Fraction = 1/2000, Comparison Frequency = 20 MHz, RF_CPG = 7, DITH = 0, VCO Frequency = 3 GHz, and a 4th Order Modulator (FM = 0). These are relatively consistent over tuning range.

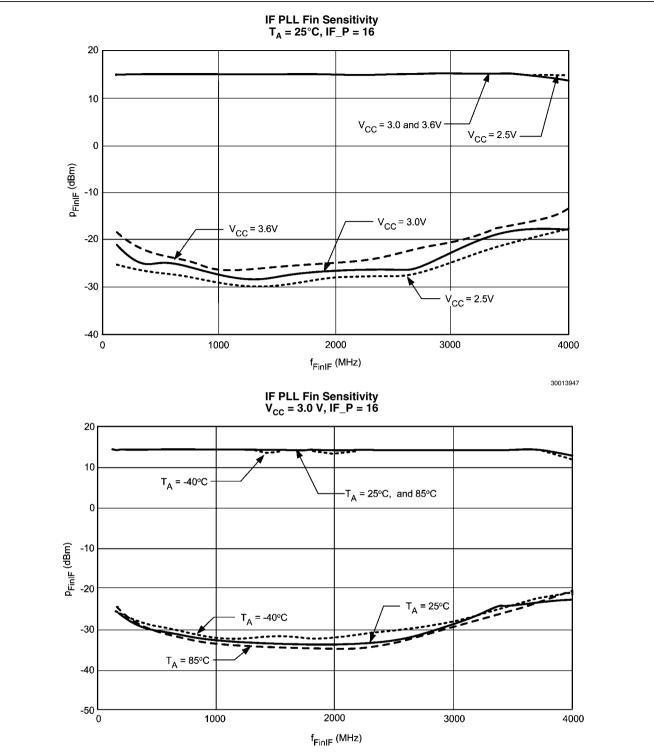
Note 6: Normalized Phase Noise Contribution is defined as: $L_N(f) = L(f) - 20log(N) - 10log(f_{COMP})$ where L(f) is defined as the single side band phase noise measured at an offset frequency, f, in a 1 Hz Bandwidth. The offset frequency, f, must be chosen sufficiently smaller than the PLL loop bandwidth, yet large enough to avoid substantial phase noise contribution from the reference source. Measurement conditions are: Offset Frequency = 11 kHz, Loop Bandwidth = 100 kHz for RF_CPG = 7, Fraction = 1/2000, Comparison Frequency = 20 MHz, FM = 0, DITH = 0, VCO Frequency = 3 GHz.

MICROWIRE INPUT TIMING DIAGRAM



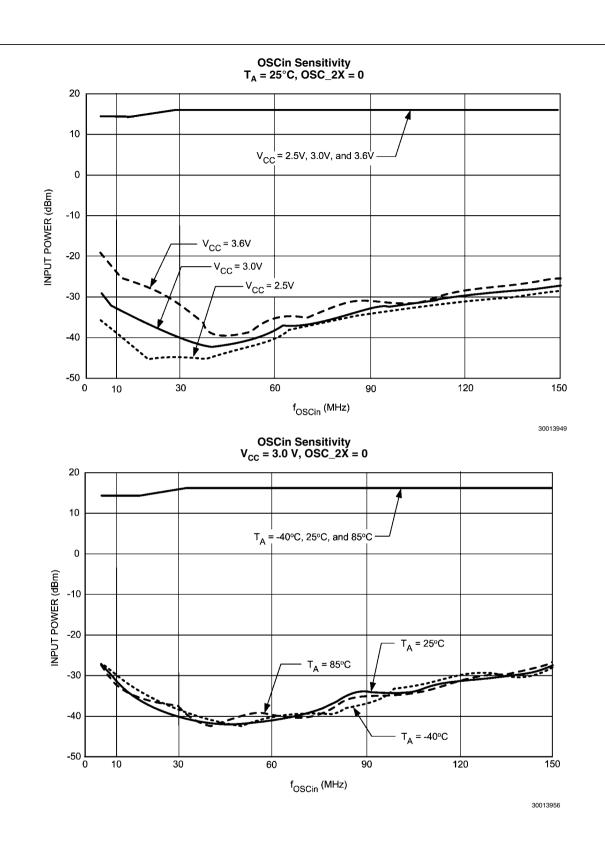
www.national.com



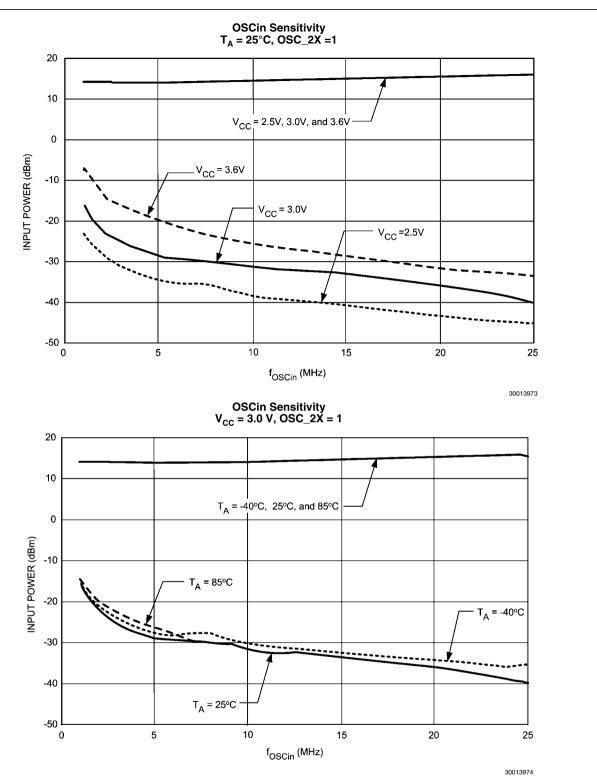


30013948

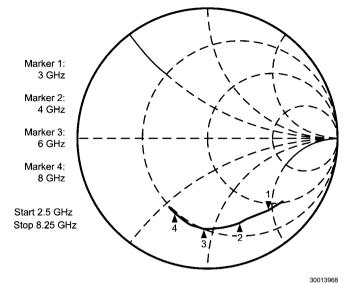




8



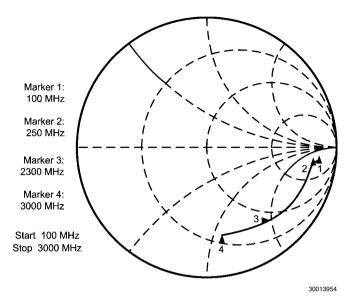
Typical Performance Characteristic : FinRF Input Impedance (Note 7)



0013968	
---------	--

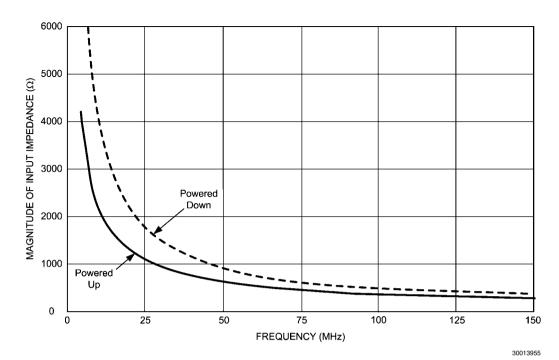
	FinRF Input Impedance	
Frequency (MHz)	Real (Ohms)	Imaginary (Ohms)
3000	39	-94
3200	37	-86
3400	33	-78
3600	30	-72
3800	28	-69
4000	26	-66
4250	24	-63
4500	23	-60
4750	22	-57
5000	20	-54
5250	19	-50
5500	18	-49
5750	17	-47
6000	17	-45
6250	16	-44
6500	16	-42
6750	16	-40
7000	16	-39
7250	16	-37
7500	16	-35
7750	17	-33
8000	17	-30
8250	16	-27

Typical Performance Characteristic : FinIF Input Impedance (Note 7)

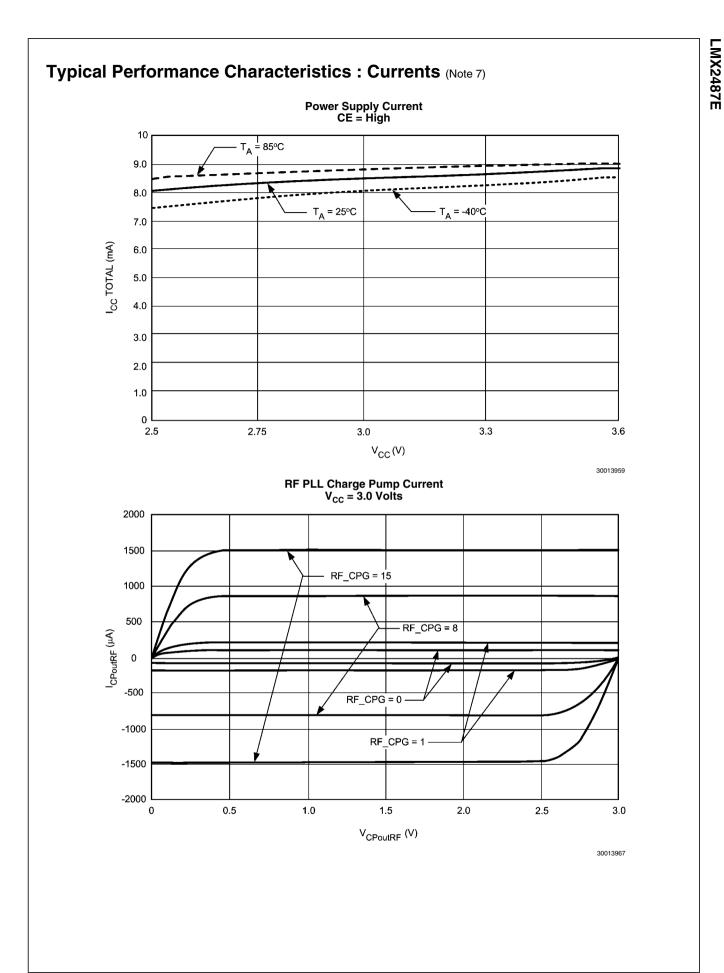


	FinIF Input Impedance	
Frequency (MHz)	Real (Ohms)	Imaginary (Ohms)
100	508	-233
150	456	-215
200	420	-206
250	403	-205
300	370	-207
400	344	-215
500	207	-223
600	274	-225
700	242	-225
800	242	-225
900	214	-222
1000	171	-208
1200	137	-191
1400	112	-176
1600	91	-158
1800	76	-139
2000	62	-122
2200	51	-105
2300	46	-96
2400	42	-88
2600	37	-74
2800	29	-63
3000	25	-54

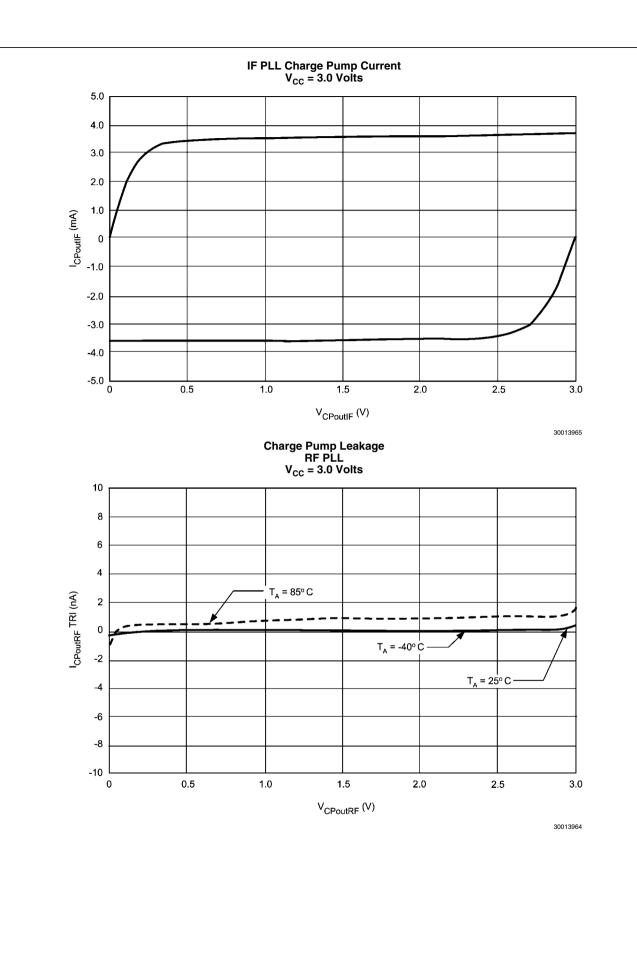
Typical Performance Characteristic : OSCin Input Impedance (Note 7)

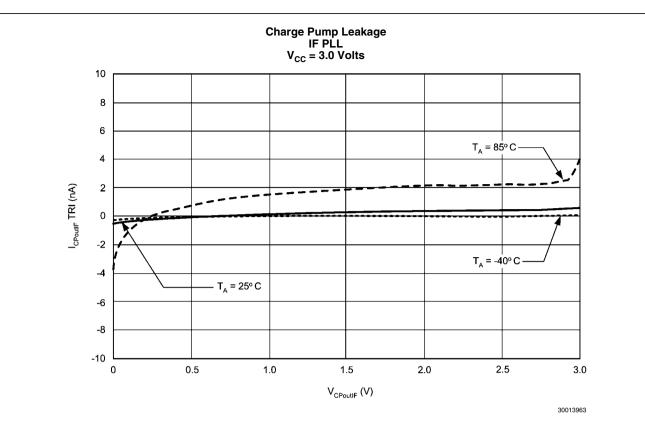


Frequency (MHz)		Powered Up				
	Real	Imaginary	Magnitude	Real	Imaginary	Magnitude
5	1730	-3779	4157	392	-8137	8146
10	846	-2236	2391	155	-4487	4490
20	466	-1196	1284	107	-2215	2217
30	351	-863	932	166	-1495	-1504
40	316	-672	742	182	-1144	1158
50	278	-566	631	155	-912	925
60	261	-481	547	153	-758	774
70	252	-425	494	154	-652	669
80	239	-388	456	147	-576	595
90	234	-358	428	145	-518	538
100	230	-337	407	140	-471	492
110	225	-321	392	138	-436	458
120	219	-309	379	133	-402	123
130	214	-295	364	133	-374	397
140	208	-285	353	132	-349	373
150	207	-279	348	133	-329	355





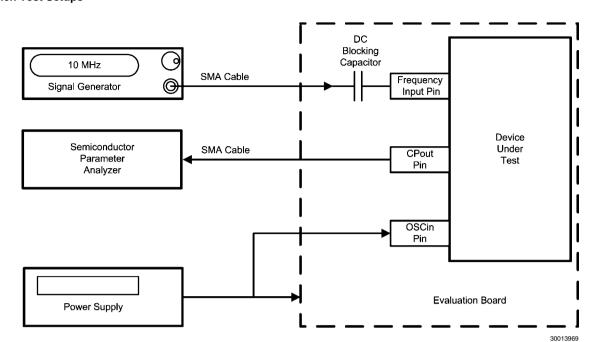




Note 7: Typical performance characteristics do not imply any sort of guarantee. Guaranteed specifications are in the electrical characteristics section.

Bench Test Setups

LMX2487E

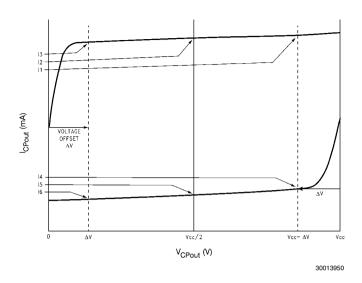


Charge Pump Current Measurement Procedure

The above block diagram shows the test procedure for testing the RF and IF charge pumps. These tests include absolute current level, mismatch, and leakage measurement. In order to measure the charge pump currents, a signal is applied to the high frequency input pins. The reason for this is to guarantee that the phase detector gets enough transitions in order to be able to change states. If no signal is applied, it is possible that the charge pump current reading will be low due to the fact that the duty cycle is not 100%. The OSCin Pin is tied to the supply. The charge pump currents can be measured by simply programming the phase detector to the necessary polarity. For instance, in order to measure the RF charge pump, a 10 MHz signal is applied to the FinRF pin. The source current can be measured by setting the RF PLL phase detector to a positive polarity, and the sink current can be measured by setting the phase detector to a negative polarity. The IF PLL currents can be measured in a similar way. Note that the magnitude of the RF PLL charge pump current is controlled by the RF_CPG bit. Once the charge pump currents are known, the mismatch can be calculated as well. In order to measure leakage, the charge pump is set to a TRI-STATE mode by enabling the RF_CPT and IF_CPT bits. The table below shows a summary of the various charge pump tests.

Current Test	RF_CPG	RF_CPP	RF_CPT	IF_CPP	IF_CPT
RF Source	0 to 15	0	0	Х	Х
RF Sink	0 to 15	1	0	Х	Х
RF TRI-STATE	Х	Х	1	Х	Х
IF Source	Х	Х	Х	0	0
IF Sink	Х	Х	Х	1	0
IF TRI-STATE	Х	Х	Х	Х	1

Charge Pump Current Specification Definitions



I1 = Charge Pump Sink Current at V_{CPout} = Vcc - ΔV

I2 = Charge Pump Sink Current at V_{CPout} = Vcc/2

I3 = Charge Pump Sink Current at $V_{CPout} = \Delta V$

I4 = Charge Pump Source Current at $V_{CPout} = Vcc - \Delta V$

I5 = Charge Pump Source Current at $V_{CPout} = Vcc/2$

I6 = Charge Pump Source Current at $V_{CPout} = \Delta V$

 ΔV = Voltage offset from the positive and negative supply rails. Defined to be 0.5 volts for this part.

 v_{CPout} refers to either $V_{CPoutRF}$ or $V_{CPoutIF}$

I_{CPout} refers to either I_{CPoutRF} or I_{CPoutIF}

Charge Pump Output Current Variation vs. Charge Pump Output Voltage

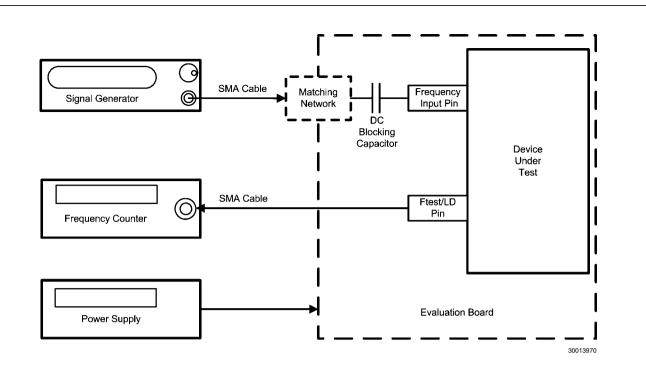
$$V_{CPout}$$
 Vs $V_{CPout} = \frac{(|1| - |13|)}{(|1| + |13|)} \times 100\%$
= $\frac{(|14| - |16|)}{(|14| + |16|)} \times 100\%$
30013951

Charge Pump Sink Current vs. Charge Pump Output Source Current Mismatch

$$I_{CPout}$$
 Sink Vs I_{CPout} Source = $\frac{||2| - ||5|}{\frac{1}{2}(||2| + ||5|)} \times 100\%$

Charge Pump Output Current Variation vs. Temperature

$$I_{CPout} V_{s} T_{A} = \frac{|I_{2}||_{T_{A}} - |I_{2}||_{T_{A} = 25^{\circ}C}}{|I_{2}||_{T_{A} = 25^{\circ}C}} \times 100\%$$
$$= \frac{|I_{5}||_{T_{A}} - |I_{5}||_{T_{A} = 25^{\circ}C}}{|I_{5}||_{T_{A} = 25^{\circ}C}} \times 100\%$$
30013953

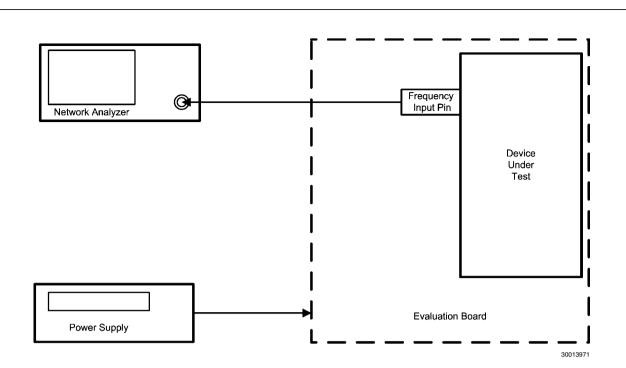


Frequency Input Pin	DC Blocking Capacitor	Corresponding Counter	Default Counter Value	MUX Value
OSCin	1000 pF	RF_R / 2	50	14
FinRF	100 pF// 1000 pF	RF_N / 2	502 + 2097150 / 4194301	15
FinIF	100 pF	IF_N / 2	534	13
OSCin	1000 pF	IF_R / 2	50	12

Sensitivity Measurement Procedure

Sensitivity is defined as the power level limits beyond which the output of the counter being tested is off by 1 Hz or more of its expected value. It is typically measured over frequency, voltage, and temperature. In order to test sensitivity, the MUX[3:0] word is programmed to the appropriate value. The counter value is then programmed to a fixed value and a frequency counter is set to monitor the frequency of this pin. The expected frequency at the Ftest/LD pin should be the signal generator frequency divided by twice the corresponding counter value. The factor of two comes in because the LMX2487E has a flip-flop which divides this frequency by two to make the duty cycle 50% in order to make it easier to read with the frequency counter. The frequency counter input impedance should be set to high impedance. In order to perform the measurement, the temperature, frequency, and voltage is set to a fixed value and the power level of the signal is varied. Note that the power level at the part is assumed to be 4 dB less than the signal generator power level. This accounts for 1 dB for cable losses and 3 dB for the pad. The power level range where the frequency is correct at the Ftest/LD pin to within 1 Hz accuracy is recorded for the sensitivity limits. The temperature, frequency, and voltage can be varied in order to produce a family of sensitivity curves. Since this is an open-loop test, the charge pump is set to TRI-STATE and the unused side of the PLL (RF or IF) is powered down when not being tested. For this part, there are actually four frequency input pins, although there is only one frequency test pin (Ftest/LD). The conditions specific to each pin are shown in above table.

Note that for the RF N counter, a fourth order fractional modulator is used in 22-bit mode with a fraction of 2097150 / 4194301 is used. The reason for this long fraction is to test the RF N counter and supporting fractional circuitry as completely as possible.



Input Impedance Measurement Procedure

The above block diagram shows the test setup used for measuring the input impedance for the LMX2487E. The DC blocking capacitor used between the input SMA connector and the pin being measured must be changed to a zero Ohm resistor. This procedure applies to the FinRF, FinIF, and OSCin pins. The basic test procedure is to calibrate the network analyzer, ensure that the part is powered up, and then measure the input impedance. The network analyzer can be calibrated by using either calibration standards or by soldering resistors directly to the evaluation board. An open can be implemented by putting no resistor, a short can be implemented by soldering a zero ohm resistor as close as possible to the pin being measured, and a short can be implemented by soldering two 100 ohm resistors in parallel as close as possible to the pin being measured. Calibration is done with the PLL removed from the PCB. This requires the use of a clamp down fixture that may not always be generally available. If no clamp down fixture is available, then this procedure can be done by calibrating up to the point where the DC blocking capacitor usually is, and then implementing port extensions with the network analyzer. Zero ohm resistor is added back for the actual measurement. Once the setup is calibrated, it is necessary to ensure that the PLL is powered up. This can be done by toggling the power down bits (RF PD and IF PD) and observing that the current consumption indeed increases when the bit is disabled. Sometimes it may be necessary to apply a signal to the OSC in pin in order to program the part. If this is necessary, disconnect the signal once it is established that the part is powered up. It is useful to know the input impedance of the PLL for the purposes of debugging RF problems and designing matching networks. Another use of knowing this parameter is make the trace width on the PCB such that the input impedance of this trace matches the real part of the input impedance of the PLL frequency of operation. In general, it is good practice to keep trace lengths short and make designs that are relatively resistant to variations in the input impedance of the PLL.

Functional Description (Note 8)

1.0 GENERAL

The LMX2487E consists of integrated N counters, R counters, and charge pumps. The TCXO, VCO and loop filter are supplied external to the chip. The various blocks are described below.

1.1 TCXO, OSCILLATOR BUFFER, AND R COUNTER

The oscillator buffer must be driven single-ended by a signal source, such as a TCXO. The OSCout pin is included to provide a buffered output of this input signal and is active when the OSC_OUT bit is set to one. The ENOSC pin can be also pulled high to ensure that the OSCout pin is active, regardless of the status of the registers in the LMX2487E.

The R counter divides this TCXO frequency down to the comparison frequency.

1.2 PHASE DETECTOR

The maximum phase detector operating frequency for the IF PLL is straightforward, but it is a little more involved for the RF PLL since it is fractional. The maximum phase detector frequency for the LMX2487E RF PLL is 50 MHz. However, this is not possible in all circumstances due to illegal divide ratios of the N counter. The crystal reference frequency also limits the phase detector frequency, although the doubler helps with this limitation. There are trade-offs in choosing the phase noise will be lower, but lock time may be increased due to cycle slipping and the capacitors in the loop filter may become rather large.

1.3 CHARGE PUMP

For the majority of the time, the charge pump output is high impedance, and the only current through this pin is the Tri-State leakage. However, it does put out fast correction pulses that have a width that is proportional to the phase error presented at the phase detector.

The charge pump converts the phase error presented at the phase detector into a correction current. The magnitude of this current is theoretically constant, but the duty cycle is proportional to the phase error. For the IF PLL, this current is not programmable, but for the RF PLL it is programmable in 16 steps. Also, the RF PLL allows for a higher charge pump current to be used when the PLL is locking in order to reduce the lock time.

1.4 LOOP FILTER

The loop filter design can be rather involved. In addition to the regular constraints and design parameters, delta-sigma PLLs have the additional constraint that the order of the loop filter should be one greater than the order of the delta sigma modulator. This rule of thumb comes from the requirement that the loop filter must roll off the delta sigma noise at 20 dB/decade faster than it rises. However, since the noise can not have infinite power, it must eventually roll off. If the loop bandwidth is narrow, this requirement may not be necessary. For the purposes of discussion in this datasheet, the pole of the loop filter at 0 Hz is not counted. So a second order filter has 3 components, a 3rd order loop filter has 5 components, and the 4th order loop filter has 7 components. Although a 5th order loop filter is theoretically necessary for use with a 4th order modulator, typically a 4th order filter is used in this case. The loop filter design, especially for higher orders can be rather involved, but there are many simulation tools and references available, such as the one given at the end of the functional description block.

1.5 N COUNTERS AND HIGH FREQUENCY INPUT PINS

The N counter divides the VCO frequency down to the comparison frequency. Because prescalers are used, there are limitations on how small the N value can be. The N counters are discussed in greater depth in the programming section. Since the input pins to these counters (FinRF and FinIF) are high frequency, layout considerations are important.

High Frequency Input Pins, FinRF and FinIF

It is generally recommended that the VCO output go through a resistive pad and then through a DC blocking capacitor before it gets to these high frequency input pins. If the trace length is sufficiently short (< 1/10th of a wavelength), then the pad may not be necessary, but a series resistor of about 39 ohms is still recommended to isolate the PLL from the VCO. The DC blocking capacitor should be chosen at least to be 27 pF. It may turn out that the frequency is above the selfresonant frequency of the capacitor, but since the input impedance of the PLL tends to be capacitive, it actually is a benefit to exceed the tune frequency. The pad and the DC blocking capacitor should be placed as close to the PLL as possible

Complementary High Frequency Pin, FinRF*

These inputs may be used to drive the PLL differentially, but it is very common to drive the PLL in a single ended fashion. A shunt capacitor should be placed at the FinRF* pin. The value of this capacitor should be chosen such that the impedance, including the ESR of the capacitor, is as close to an AC short as possible at the operating frequency of the PLL. 100 pF is a typical value.

1.6 POWER PINS, POWER DOWN, AND POWER UP MODES

It is recommended that all of the power pins be filtered with a series 18 ohm resistor and then placing two capacitors shunt to ground, thus creating a low pass filter. Although it makes sense to use large capacitor values in theory, the ESR (Equivalent Series Resistance) is greater for larger capacitors. For optimal filtering minimize the sum of the ESR and theoretical impedance of the capacitors. It is therefore recommended to provide two capacitors of very different sizes for the best filtering. 1 μ F and 100 pF are typical values. The small capacitor should be placed as close as possible to the pin.

The power down state of the LMX2487E is controlled by many factors. The one factor that overrides all other factors is the CE pin. If this pin is low, the part will be powered down. Asserting a high logic level on this pin is necessary to power up the chip, however, there are other bits in the programming registers that can override this and put the PLL back in a power down state. Provided that the voltage on the CE pin is high, programming the RF_PD and IF_PD bits to zero guarantees that the part will be powered up. Programming either one of these bits to one will power down the appropriate section of the synthesizer, provided that the ATPU bit does not override this.

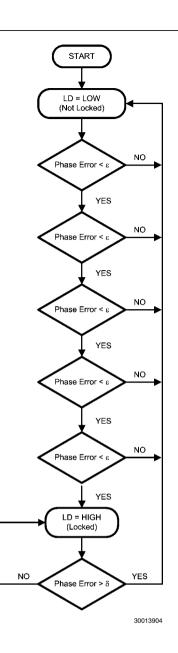
CE Pin	RF_PD	ATPU Bit Enabled + Write to RF N Counter	PLL State
Low	х	х	Powered Down (Asynchronous)
High	Х	Yes	Powered Up
High	0	No	Powered Up
High	1	No	Powered Down (Asynchronous)

1.7 DIGITAL LOCK DETECT OPERATION

The RF PLL digital lock detect circuitry compares the difference between the phase of the inputs of the phase detector to a RC generated delay of ε . To indicate a locked state (Lock = HIGH) the phase error must be less than the ε RC delay for 5 consecutive reference cycles. Once in lock (Lock = HIGH), the RC delay is changed to approximately δ . To indicate an out of lock state (Lock = LOW), the phase error must become greater δ . The values of ε and δ are dependent on which PLL is used and are shown in the table below:

PLL	ε	δ
RF	10 ns	20 ns
IF	15 ns	30 ns

When the PLL is in the power down mode and the Ftest/LD pin is programmed for the lock detect function, it is forced LOW. The accuracy of this circuit degrades at higher comparison frequencies. To compensate for this, the DIV4 word should be set to one if the comparison frequency exceeds 20 MHz. The function of this word is to divide the comparison frequency presented to the lock detect circuit by 4. Note that if the MUX[3:0] word is set such as to view lock detect for both PLLs, an unlocked (LOW) condition is shown whenever either one of the PLLs is determined to be out of lock.



1.8 CYCLE SLIP REDUCTION AND FASTLOCK

The LMX2487E offers both cycle slip reduction (CSR) and Fastlock with timeout counter support. This means that it requires no additional programming overhead to use them. It is generally recommended that the charge pump current in the steady state be 8X or less in order to use cycle slip reduction, and 4X or less in steady state in order to use Fastlock. The next step is to decide between using Fastlock or CSR. This determination can be made based on the ratio of the comparison frequency ($f_{\rm COMP}$) to loop bandwidth (BW).

Comparison Frequency (f _{COMP})	Fastlock	Cycle Slip Reduction (CSR)
f _{COMP} ≤ 1.25 MHz	Noticeable better than CSR	Likely to provide a benefit, provided
1.25 MHz < f _{COMP} ≤ 2 MHz	Marginally better than CSR	that f _{COMP} > 100 X BW
f _{COMP} > 2 MHz	Same or worse than CSR	

Cycle Slip Reduction (CSR)

Cycle slip reduction works by reducing the comparison frequency during frequency acquisition while keeping the same loop bandwidth, thereby reducing the ratio of the comparison frequency to the loop bandwidth. In cases where the ratio of the comparison frequency exceeds about 100 times the loop bandwidth, cycle slipping can occur and significantly degrade lock times. The greater this ratio, the greater the benefit of CSR. This is typically the case of high comparison frequencies. In circumstances where there is not a problem with cycle slipping, CSR provides no benefit. There is a glitch when CSR is disengaged, but since CSR should be disengaged long before the PLL is actually in lock, this glitch is not an issue. A good rule of thumb for CSR disengagement is to do this at the peak time of the transient response. Because this time is typically much sooner than Fastlock should be disengaged, it does not make sense to use CSR and Fastlock in combination.

Fastlock

Fastlock works by increasing the loop bandwidth only during frequency acquisition. In circumstances where the comparison frequency is less than or equal to 2 MHz, Fastlock may provide a benefit beyond what CSR can offer. Since Fastlock also reduces the ratio of the comparison frequency to the loop bandwidth, it may provide a significant benefit in cases where the comparison frequency is above 2 MHz. However, CSR can usually provide an equal or larger benefit in these cases, and can be implemented without using an additional resistor. The reason for this restriction on frequency is that Fastlock has a glitch when it is disengaged. As the time of engagement for Fastlock decreases and becomes on the order of the fast lock time, this glitch grows and limits the benefits of Fastlock. This effect becomes worse at higher comparison frequencies. There is always the option of reducing the comparison frequency at the expense of phase noise in order to satisfy this constraint on comparison frequency. Despite this glitch, there is still a net improvement in lock time using Fastlock in these circumstances. When using Fastlock, it is also recommended that the steady state charge pump state be 4X or less. Also, Fastlock was originally intended only for second order filters, so when implementing it with higher order filters, the third and fourth poles can not be too close in, or it will not be possible to keep the loop filter well optimized when the higher charge pump current and Fastlock resistor are engaged.

1.8.1 Using Cycle Slip Reduction (CSR) to Avoid Cycle Slipping

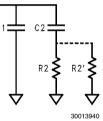
Once it is decided that CSR is to be used, the cycle slip reduction factor needs to be chosen. The available factors are 1/2, 1/4, and 1/16. In order to preserve the same loop characteristics, it is recommended that the following constraint be satisfied:

(Fastlock Charge Pump Current) / (Steady State Charge Pump Current) = CSR

In order to satisfy this constraint, the maximum charge pump current in steady state is 8X for a CSR of 1/2, 4X for a CSR of 1/4, and 1X for a CSR of 1/16. Because the PLL phase noise is better for higher charge pump currents, it makes sense to choose CSR only as large as necessary to prevent cycle slipping. Choosing it larger than this will not improve lock time, and will result in worse phase noise.

Consider an example where the desired loop bandwidth in steady state is 100 kHz and the comparison frequency is 20 MHz. This yields a ratio of 200. Cycle slipping may be present, but would not be too severe if it was there. If a CSR factor of 1/2 is used, this would reduce the ratio to 100 during frequency acquisition, which is probably sufficient. A charge pump current of 8X could be used in steady state, and a factor of 16X could be used during frequency acquisition. This yields a ratio of 1/2, which is equal to the CSR factor and this satisfies the above constraint. In this circumstance, it could also be decided to just use 16X charge pump current all the time, since it would probably have better phase noise, and the degradation in lock time would not be too severe.

1.8.2 Using Fastlock to Improve Lock Times



Once it is decided that Fastlock is to be used, the loop bandwidth multiplier, K, is needed in order to determine the theoretical impact of Fastlock on the loop bandwidth and the resistor value, R2p, that is switched in parallel during Fastlock. This ratio is calculated as follows:

K = (Fastlock Charge Pur	np Current) / (Steady State
Charge Pump Current)	

•			
к	Loop Bandwidth	R2p Value	Lock Time
1	1.00 X	Open	100 %
2	1.41 X	R2/0.41	71 %
3	1.73 X	R2/0.73	58%
4	2.00 X	R2	50%
8	2.83 X	R2/1.83	35%
9	3.00 X	R2/2	33%
16	4.00 X	R2/3	25%

The above table shows how to calculate the fastlock resistor and theoretical lock time improvement, once the ratio , K, is known. This all assumes a second order filter (not counting the pole at 0 Hz). However, it is generally recommended that the loop filter order be one greater than the order of the delta sigma modulator, which means that a second order filter is never recommended. In this case, the value for R2p is typically about 80% of what it would be for a second order filter. Because the fastlock disengagement glitch gets larger and it is harder to keep the loop filter optimized as the K value becomes larger, designing for the largest possible value for K usually, but not always yields the best improvement in lock time. To get a more accurate estimate requires more simulation tools, or trial and error.

1.8.3 Capacitor Dielectric Considerations for Lock Time

The LMX2487E has a high fractional modulus and high charge pump gain for the lowest possible phase noise. One consideration is that the reduced N value and higher charge pump may cause the capacitors in the loop filter to become larger in value. For larger capacitor values, it is common to have a trade-off between capacitor dielectric guality and physical size. Using film capacitors or NPO/COG capacitors yields the best possible lock times, where as using X7R or Z5R capacitors can increase lock time by 0-500%. However, it is a general tendency that designs that use a higher compare frequency tend to be less sensitive to the effects of capacitor dielectrics. Although the use of lesser quality dielectric capacitors may be unavoidable in many circumstances, allowing a larger footprint for the loop filter capacitors, using a lower charge pump current, and reducing the fractional modulus are all ways to reduce capacitor values. Capacitor dielectrics have very little impact on phase noise and spurs.

1.9 FRACTIONAL SPUR AND PHASE NOISE CONTROLS

Control of the fractional spurs is more of an art than an exact science. The first differentiation that needs to be made is between primary fractional and sub-fractional spurs. The primary fractional spurs are those that occur at increments of the channel spacing only. The sub-fractional spurs are those that occur at a smaller resolution than the channel spacing, usually one-half or one-fourth. There are trade-offs between fractional spurs, sub-fractional spurs, and phase noise. The rules of thumb presented in this section are just that. There will be exceptions. The bits that impact the fractional spurs are FM and DITH, and these bits should be set in this order.

The first step to do is choose FM, for the delta sigma modulator order. It is recommended to start with FM = 3 for a third order modulator and use strong dithering. In general, there is a trade-off between primary and sub-fractional spurs. Choosing the highest order modulator (FM = 0 for 4th order) typically provides the best primary fractional spurs, but the worst subfractional spurs. Choosing the lowest modulator order (FM = 2 for 2nd order), typically gives the worst primary fractional spurs, but the best sub-fractional spurs. Choosing FM = 3, for a 3rd order modulator is a compromise.

The second step is to choose DITH, for dithering. Dithering has a very small impact on primary fractional spurs, but a much larger impact on sub-fractional spurs. The only problem is that it can add a few dB of phase noise, or even more if the loop bandwidth is very wide. Disabling dithering (DITH = 0), provides the best phase noise, but the sub-fractional spurs are worst (except when the fractional numerator is 0, and in this case, they are the best). Choosing strong dithering (DITH = 2) significantly reduces sub-fractional spurs, if not eliminating them completely, but adds the most phase noise. Weak dithering (DITH = 1) is a compromise.

The third step is to tinker with the fractional word. Although 1/10 and 400/4000 are mathematically the same, expressing fractions with much larger fractional numerators often improve the fractional spurs. Increasing the fractional denominator only improves spurs to a point. A good practical limit could be to keep the fractional denominator as large as possible, but not to exceed 4095, so it is not necessary to use the extended fractional numerator or denominator.

Note 8: For more information concerning delta-sigma PLLs, loop filter design, cycle slip reduction, Fastlock, and many other topics, visit wireless.national.com. Here there is the EasyPLL simulation tool and an online reference called "PLL Performance, Simulation, and Design", by Dean Banerjee.

Programming Description

2.0 GENERAL PROGRAMMING INFORMATION

The 24-bit data registers are loaded through a MICROWIRE Interface. These data registers are used to program the R counter, the N counter, and the internal mode control latches. The data format of a typical 24-bit data register is shown below. The control bits CTL [3:0] decode the register address. On the rising edge of LE, data stored in the shift register is loaded into one of the appropriate latches (selected by address bits). Data is shifted in MSB first. Note that it is best to program the N counter last, since doing so initializes the digital lock detector and Fastlock circuitry. Note that initialize means it resets the counters, but it does NOT program values into these registers. The exception is when 22-bit is not being used. In this case, it is not necessary to program the R7 register.

MSB	LSB
DATA [21:0]	CTL [3:0]
23 4	3 210

2.0.1 Register Location Truth Table

The control bits CTL [3:0] decode the internal register address. The table below shows how the control bits are mapped to the target control register.

C3	C2	C1	CO	DATA Location
х	х	x	0	R0
0	0	1	1	R1
0	1	0	1	R2
0	1	1	1	R3
1	0	0	1	R4
1	0	1	1	R5
1	1	0	1	R6
1	1	1	1	R7

2.0.2 Control Register Content Map

Because the LMX2487E registers are complicated, they are organized into two groups, basic and advanced. The first four registers are basic registers that contain critical information necessary for the PLL to achieve lock. The last 5 registers are for features that optimize spur, phase noise, and lock time performance. The next page shows these registers.

			-	er Ma		hod th	ot the			tually	, toko	adva	ntogo	of all	tho r	nodo	o of th		12010	75 +		uiok c	start re	aistor
map	is sh	own ii	n orde	er for t	he us	er to g	jet the	e part	up an	id rur	ining o	quickl	y usin	g only	thos	e bits	critic	al for	basic	funct	ionali	ty. T	he foll	owing
defa	ult co	onditic	ns fo	r this I	orogra	ammir	ng sta	te are	e a thi	rd or	der de	elta-si	gma r	nodul	ator i	n 12-	bit mo	de w	ith no	dithe	ering a	and I	no Fas	tlock.
RE G	23	22	21	20	19	18	17 1	6 1	5 1	4 1	3 1	2 11	10	9	8	7	6	5	4	;	3	2	1	0
					DAT	A[19:0)](E	cept	for th	e RF	_N Re	egiste	r, whi	ch is	[22:0])				C	3 (22	C1	C0
R0					RF_I	V[10:0)]								F	F_FI	V[11:C)]			•			0
R1	RF_PD	RF_P		R	F_R[5:0]							RF_	_FD[1	1:0]					(b	0	1	1
R2	PDF	I								IF_N	N[18:0]								(D C	1	0	1
R3		000)1		RF	_CPG	i[3:0]						IF_	_R[11	:0]					(2	1	1	1
R4	0	0	1	0	0	0	0	0	1 -	1 (0 0	0	1	1	1	0	0	0	0		1	0	0	1
Corr	plete	e Reg	ister	Мар																				
	-	-	Register Map te register map shows all the functionality of all registers, including the last five.																					
RE G	23	22	21	20	19	18	17	16	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
					DA	TA[19	9:0] (Exce	ot for	the F	F_N	_N Register, which is [22:0])											2 C1	CO
R0					RF	_N[10):0]									F	RF_FN	V[11:0)]					0
R1	RF _P D	RF _P			RF_F	R[5:0]						RF_FD[11:0]										0	1	1
R2	IF_ PD									IF	_N[18	8:0]									0	1	0	1
R3		ACCE	55[3	·01	Б	F_CF	PG[3·	ומ						IF_R[11.01						0	1	1	1
R4	ATPU	0	1	0	0	0	Dľ	TH :0]		M :0]	0	OSC_2X	osc_out		RF_CPP	а ш			JX :0]		1	0	0	1
D <i>r</i>						101.1	01					0	Ő			[01.1								$\left \right $
R5 R6	<u></u>	R[1:0]		RF_CI			<u>~]</u>					Þ	F_TO		F_FN 01	[∠۱.۱	<u> </u>				1	0	1	1
R7	0	0	0		0	0	0	0	0	0	DIV4	0	1	0	0	1	RST	RST	CPT	RF_CPT	1	1	1	1
																	╘	Ц Ш	⊑					

2.1 R0 REGISTER

Note that this register has only one control bit, so the N counter value to be changed with a single write statement to the PLL.

REGISTER	23	22	21	20	19	18	17	16	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
		DATA[22:0]														C0								
R0		RF_N[10:0]													R	F_F	N[1	1:0]						0

2.1.1 RF_FN[11:0] -- Fractional Numerator for RF PLL

Refer to section 2.6.1 for a more detailed description of this control word.

2.1.2 RF_N[10:0] -- RF N Counter Value

The RF N counter contains an 16/17/20/21 and a 32/33/36/37 prescaler. The N counter value can be calculated as follows:

 $N = RF_P \cdot RF_C + 4 \cdot RF_B + RF_A$

 $RF_C \ge Max\{RF_A, RF_B\}$, for N-2^{FM}-1 ... N+2^{FM} is a necessary condition. This rule is slightly modified in the case where the RF_B counter has an unused bit, where this extra bit is used by the delta-sigma modulator for the purposes of modulation. Consult the tables below for valid operating ranges for each prescaler.

Operation with the 16/17/20/21 Prescaler (RF_P=0)

RF_N					F	RF_N [10:0)]								
			RF_C	; [5:0]			I	RF_B [2:0]	RF_A	. [1:0]				
<49					N Values	Below 49	are Illegal								
49-63					Legal [Divide Rat	ios are:								
	2nd Order Modulator: 49-61														
	3rd Order Modulator: 51-59														
	4th Order Modulator: 55														
64-79	Legal Divide Ratios are:														
				2	nd and 3rd	d Order M	odulator: A	A II							
					4th Orde	r Modulat	or: 64-75								
80	0	0	0	1	0	1	0	0	0	0	0				
			-				0								
1023	1	1	1	1	1	1	0	1	1	1	1				
>1023				N v	alues abo	ve 1023 a	re prohibi	ted.							

Operation with the 32/33/36/37 Prescaler (RF_P=1)

DE N					F	RF_N [10:0)]									
RF_N			RF_C	; [5:0]			F	RF_B [2:0)]	RF_4	A [1:0]					
<97				N Va	lues Belov	v 97 are II	legal.									
97-226					Legal [Divide Rati	ios are:									
			2nd Orde	er Modulat	or: 97-109	9, 129-145	, 161-181	, 193-217	, 225-226							
		3rd Order Modulator: 99-107, 131-143, 163-179, 195-215 4th Order Modulator: 103, 135-139, 167-175, 199-211 Legal Divide Ratios are: 2nd and 3rd Order Modulator: All														
227230																
					4th Orde	er Modulat	or: None									
231	0	0	0	1	1	1	0	0	1	1	1					
	-			-	-			-								
2039	1	1	1	1	1	1	1	0	1	1	1					
2040-2043			Pos	sible with	a second	or third or	der delta-	sigma eng	gine.							
2044-2045			Po	ossible onl	y with a s	econd ord	er delta-si	gma engir	ne.							
>2045				N valu	es greate	r than 204	5 are proh	ibited.								

2.2 R1 REGI	STER																								
REGISTER	23	22	21	20	19	18	17	16	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0	
		DATA[19:0]														C3	C2	C1	C0						
R1	RF_PD	RF_PD RF_P RF_R[5:0] RF_FD[11:0]														0	0	1	1						

2.2.1 RF_FD[11:0] -- RF PLL Fractional Denominator

The function of these bits are described in section 2.6.2.

2.2.2 RF_R [5:0] -- RF R Divider Value

The RF R Counter value is determined by this control word. Note that this counter does allow values down to one.

R Value			RF_F	R[5:0]		
1	0	0	0	0	0	1
63	1	1	1	1	1	1

2.2.3 RF_P -- RF Prescaler bit

The prescaler used is determined by this bit.

RF_P	Prescaler	Maximum Frequency
0	16/17/20/21	4000 MHz
1	32/33/36/37	6000 MHz

2.2.4 RF_PD -- RF Power Down Control Bit

When this bit is set to 0, the RF PLL operates normally. When it is set to one, the RF PLL is powered down and the RF Charge pump is set to a TRI-STATE mode. The CE pin and ATPU bit also control power down functions, and will override the RF_PD bit. The order of precedence is as follows. First, if the CE pin is LOW, then the PLL will be powered down. Provided this is not the case, the PLL will be powered up if the ATPU bit says to do so, regardless of the state of the RF_PD bit. After the CE pin and the ATPU bit are considered, then the RF_PD bit then takes control of the power down function for the RF PLL.

2.3 R2 REGISTER

REGISTER	23	22	21	20	19	18	17	16	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
		DATA[19:0]																	C3	C2	C1	C0		
R2	IF_PD								IF_	N[18	:0]										0	1	0	1

2.3.1 IF_N[18:0] -- IF N Divider Value

IF_N Counter Programming with the 8/9 Prescaler (IF_P=0)

N Value									IF	_N[18	:0]								
in value								IF_B									IF	_A	
≤23				N val	ues le	ss tha	n or eo	qual to	23 ar	e proh	ibited	becau	se IF_	B ≥ 3	is req	uired.			
24-55							Le	gal div	/ide ra	tios in	this ra	ange a	re:						
			-		_		-	24-2	27, 32-	36, 40	-45, 4	8-54	_	-	-	-	-	-	
56	0	0	0	0	0	0	0	0	0	0	0	0	1	1	1	0	0	0	0
57	0	0	0	0	0	0	0	0	0	0	0	0	1	1	1	0	0	0	1
		•	•										•						
262143	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	0	1	1	1

Operation with the 16/17 Prescaler (IF_P=1)

N Value																			
								IF_B									IF,	_A	
≤47				N val	ues le	ss tha	n or e	qual to	47 ar	e proh	ibited	becau	se IF_	B ≥ 3	is req	uired.			
48-239		Legal divide ratios in this range are:																	
		Legal divide ratios in this range are: 48-51, 64-68, 80-85, 96-102, 112-119, 128-136, 144-153, 160-170, 176-187, 192-204, 208-221, 224-238															3		
240	0	0	0	0	0	0	0	0	0	0	0	1	1	1	1	0	0	0	0
241	0	0	0	0	0	0	0	0	0	0	0	1	1	1	1	0	0	0	1
													•						
524287	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1

2.3.4 IF_PD -- IF Power Down Bit

When this bit is set to 0, the IF PLL operates normally. When it is set to 1, the IF PLL powers down and the output of the IF PLL charge pump is set to a TRI-STATE mode. If the ATPU bit is set and register R0 is written to, the IF_PD will be reset to 0 and the IF PLL will be powered up. If the CE pin is held low, the IF PLL will be powered down, overriding the IF_PD bit.

2.4 R3 REGIS	TER																								LMX2
REGISTER	23	22	21	20	19	18	17	16	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0	48
								ĺ		(19:0]										C3	C2	C1	C0	ΞE
R3	A	CCE	SS[3:	0]	R	F_CF	PG[3:	0]					IF_R	[11:0]]						0	1	1	1	

2.4.1 IF_R[11:0] -- IF R Divider Value

For the IF R divider, the R value is determined by the IF_R[11:0] bits in the R3 register. The minimum value for IF_R is 3.

R Value						IF_R	[11:0]					
3	0	0	0	0	0	0	0	0	0	0	1	1
4095	1	1	1	1	1	1	1	1	1	1	1	1

2.4.2 RF_CPG -- RF PLL Charge Pump Gain

This is used to control the magnitude of the RF PLL charge pump in steady state operation.

RF_CPG	Charge Pump State	Typical RF Charge Pump Current at 3 Volts (μA)
0	1X	95
1	2X	190
2	3X	285
3	4X	380
4	5X	475
5	6X	570
6	7X	665
7	8X	760
8	9X	855
9	10X	950
10	11X	1045
11	12X	1140
12	13X	1235
13	14X	1330
14	15X	1425
15	16X	1520

2.4.3 ACCESS -- Register Access word

It is mandatory that the first 5 registers R0-R4 be programmed. The programming of registers R5-R7 is optional. The ACCESS [3:0] bits determine which additional registers need to be programmed. Any one of these registers can be individually programmed. According to the table below, when the state of a register is in default mode, all the bits in that register are forced to a default state and it is not necessary to program this register. When the register is programmable, it needs to be programmed through the MICROWIRE. Using this register access technique, the programming required is reduced up to 37%.

ACCESS Bit	Register Location	Register Controlled
ACCESS[0]	R3[20]	Must be set to 1
ACCESS[1]	R3[21]	R5
ACCESS[2]	R3[22]	R6
ACCESS[3]	R3[23]	R7

The default conditions the registers is shown below:

Register	23	22	21	20	19	18	17	16	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
									[Data	19:0]									C3	C2	C1	С
R4									R4	Mus	t be p	orogr	amm	ied m	nanua	ally.								-
R5	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	1	0	1	—
R6	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	1	1	0	—
R7	0	0	0	0	0	0	0	0	0	0	0	0	1	0	0	1	0	0	0	0	1	1	1	—

onds to the following bit settings. One sp

Register	Bit Location	Bit Name	Bit Description	Bit Value	Bit State
	R4[23]	ATPU	Autopowerup	0	Disabled
	R4[17:16]	DITH	Dithering	2	Strong
	R4[15:16]	FM	Modulator Order	3	3rd Order
	R4[23]	OSC_2X	Oscillator Doubler	0	Disabled
	R4[23]	OSC_OUT	OSCout Pin Enable	0	Disabled
R4	R4[23]	IF_CPP	IF Charge Pump Polarity	1	Positive
	R4[23]	RF_CPP	RF Charge Pump Polarity	1	Positive
	R4[23]	IF_P	IF PLL Prescaler	1	16/17
	R4[7:4]	MUX	Ftest/LD Output	0	Disabled
R5	R5[23:14]	RF_FD[21:12]	Extended Fractional Denominator	0	Disabled
сл	R5[13:4]	RF_FN[21:12]	Extended Fractional Numerator	0	Disabled
	R6[23:22]	CSR	Cycle Slip Reduction	0	Disabled
R6	R6[21:18]	RF_CPF	Fastlock Charge Pump Current	0	Disabled
	R6[17:4]	RF_TOC	RF Timeout Counter	0	Disabled
	R7[13]	DIV4	Lock Detect Adjustment	0	Disabled (Fcomp ≤ 20 MHz)
57	R7[7]	IF_RST	IF PLL Counter Reset	0	Disabled
R7	R7[6]	RF_RST	RF PLL Counter Reset	0	Disabled
	R7[5]	IF_CPT	IF PLL Tri-State	0	Disabled
	R7[4]	RF_CPT	RF PLL Tri-State	0	Disabled

2.5 R4 REGISTER

This register controls the conditions for the RF PLL in Fastlock.

REGISTER	23	22	21	20	19	18	17 16	15	14	13	12	11	10	9	8	7 6 5 4	3	2	1	0
		•					÷		DA	TA[1	19:0]						C3	C2	C1	C0
R4	ATPU	0	1	0	0	0	DITH [1:0]	FI [1:	VI 0]	0	OSC_ 2X	OSC_ OUT	IF_ CPP	RF_ CPP	IF_P	MUX [3:0]	1	0	0	1

2.5.1 MUX[3:0] Frequency Out & Lock Detect MUX

These bits determine the output state of the Ftest/LD pin.

	MUX	[3:0]		Output Type	Output Description
0	0	0	0	High Impedance	Disabled
0	0	0	1	Push-Pull	General purpose output, Logical "High" State
0	0	1	0	Push-Pull	General purpose output, Logical "Low" State
0	0	1	1	Push-Pull	RF & IF Digital Lock Detect
0	1	0	0	Push-Pull	RF Digital Lock Detect
0	1	0	1	Push-Pull	IF Digital Lock Detect
0	1	1	0	Open Drain	RF & IF Analog Lock Detect
0	1	1	1	Open Drain	RF Analog Lock Detect
1	0	0	0	Open Drain	IF Analog Lock Detect
1	0	0	1	Push-Pull	RF & IF Analog Lock Detect
1	0	1	0	Push-Pull	RF Analog Lock Detect
1	0	1	1	Push-Pull	IF Analog Lock Detect
1	1	0	0	Push-Pull	IF R Divider divided by 2
1	1	0	1	Push-Pull	IF N Divider divided by 2
1	1	1	0	Push-Pull	RF R Divider divided by 2
1	1	1	1	Push-Pull	RF N Divider divided by 2

2.5.2 IF_P -- IF Prescaler

When this bit is set to 0, the 8/9 prescaler is used. Otherwise the 16/17 prescaler is used.

IF_P	IF Prescaler	Maximum Frequency
0	8/9	800 MHz
1	16/17	800 MHz

2.5.3 RF_CPP -- RF PLL Charge Pump Polarity

RF_CPP	RF Charge Pump Polarity
0	Negative
1	Positive (Default)

2.5.4 IF_CPP -- IF PLL Charge Pump Polarity

For a positive phase detector polarity, which is normally the case, set this bit to 1. Otherwise set this bit for a negative phase detector polarity.

IF_CPP	IF Charge Pump Polarity
0	Negative
1	Positive

2.5.5 OSC_OUT Oscillator Output Buffer Enable

OSC_OUT	OSCout Pin
0	Disabled (High Impedance)
1	Buffered output of OSCin pin

2.5.6 OSC2X -- Oscillator Doubler Enable

When this bit is set to 0, the oscillator doubler is disabled and the TCXO frequency presented to the IF R and RF R counters is equal to that of the input frequency of the OSCin pin. When this bit is set to 1, the TCXO frequency presented to the RF R counter is doubled. Phase noise added by the doubler is negligible.

OSC2X	Frequency Presented to RF R Counter	Frequency Presented to IF R Counter
0	f _{OSCin}	f _{OSCin}
1	2 x f _{OSCin}	

2.5.7 FM[1:0] -- Fractional Mode

Determines the order of the delta-sigma modulator. Higher order delta-sigma modulators reduce the spur levels closer to the carrier by pushing this noise to higher frequency offsets from the carrier. In general, the order of the loop filter should be at least one greater than the order of the delta-sigma modulator in order to allow for sufficient roll-off.

FM	Function
0	Fractional PLL mode with a 4th order delta-sigma modulator
1	Disable the delta-sigma modulator. Recommended for test use only.
2	Fractional PLL mode with a 2nd order delta-sigma modulator
3	Fractional PLL mode with a 3rd order delta-sigma modulator

2.5.8 DITH[1:0] -- Dithering Control

Dithering is a technique used to spread out the spur energy. Enabling dithering can reduce the main fractional spurs, but can also give rise to a family of smaller spurs. Whether dithering helps or hurts is application specific. Enabling the dithering may also increase the phase noise. In most cases where the fractional numerator is zero, dithering usually degrades performance.

Dithering tends to be most beneficial in applications where there is insufficient filtering of the spurs. This often occurs when the loop bandwidth is very wide or a higher order delta-sigma modulator is used. Dithering tends not to impact the main fractional spurs much, but has a much larger impact on the sub-fractional spurs. If it is decided that dithering will be used, best results will be obtained when the fractional denominator is at least 1000.

DITH	Dithering Mode Used
0	Disabled
1	Weak Dithering
2	Strong Dithering
3	Reserved

2.5.9 ATPU -- PLL Automatic Power Up

When this bit is set to 1, both the RF and IF PLL power up when the R0 register is written to. When the R0 register is written to, the PD_RF and PD_IF bits are changed to 0 in the PLL registers. The exception to this case is when the CE pin is low. In this case, the ATPU function is disabled.

2.6 R5 REGIS	TER																							
REGISTER	23	22	21	20	19	18	17	16	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
								ĺ		[19:0]							,			C3	C2	C1	C0
R5				R		RF_FN[21:12]										1	0	1	1					

2.6.1 Fractional Numerator Determination { RF_FN[21:12], RF_FN[11:0], ACCESS[1] }

In the case that the ACCESS[1] bit is 0, then the part operates in 12-bit fractional mode, and the RF_FN2[21:12] bits become do not care bits. When the ACCESS[1] bit is set to 1, the part operates in 22-bit mode and the fractional numerator is expanded from 12 to 22-bits.

Fractional				R	F_FN	[21:1	2]								Р			01						
Numerator		(Th	ese b	oits or	nly ap	ply ir	1 22-	bit m	ode)															
0											0	0	0	0	0	0	0	0	0	0	0	0		
1		In 1		mod					are.		0	0	0	0	0	0	0	0	0	0	0	1		
		In 22- bit mode, for N <4096, these bits should be all set to 0.																						
4095			11030	0113	Shour	ube		1 10 0	•		1	1	1	1	1	1	1	1	1	1	1	1		
4096	0	0	0	0	0	0	0	0	0	1	0	0	0	0	0	0	0	0	0	0	0	0		
4194303	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1		

2.6.2 Fractional Denominator Determination { RF_FD[21:12], RF_FD[11:0], ACCESS[1]}

In the case that the ACCESS[1] bit is 0, then the part is operates in the 12-bit fractional mode, and the RF_FD[21:12] bits become do not care bits. When the ACCESS[1] is set to 1, the part operates in 22-bit mode and the fractional denominator is expanded from 12 to 22-bits.

Fractional				R	F_FD	[21:1	2]				RF_FD[11:0]														
Denominator		(Th	ese b	oits or	nly ap	ply ir	n 22-	bit m	ode)																
0		In 1	2- bit	mod	e, the	ese ar	e do	not c	are.		0	0	0	0	0	0	0	0	0	0	0	0			
1					mode	,					0	0	0	0	0	0	0	0	0	0	0	1			
		t	these	bits	shoul	d be	all se	t to 0	-																
4095											1	1	1	1	1	1	1	1	1	1	1	1			
4096	0	0	0	0	0	0	0	0	0	1	0	0	0	0	0	0	0	0	0	0	0	0			
4194303	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1			

2.7 R6 REGIS	STER																							
REGISTER	23	22	21	20	19	18	17	16	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
		DATA[19:0] C3 C2 C1 C0														C0								
R6	CSR	CSR[1:0] RF_CPF[3:0] RF_TOC[13:0] 1 1 0 1														1								

2.7.1 RF_TOC -- RF Time Out Counter and Control for FLoutRF Pin

The RF_TOC[13:0] word controls the operation of the RF Fastlock circuitry as well as the function of the FLoutRF output pin. When this word is set to a value between 0 and 3, the RF Fastlock circuitry is disabled and the FLoutRF pin operates as a general purpose CMOS TRI-STATE I/O. When RF_TOC is set to a value between 4 and 16383, the RF Fastlock mode is enabled and the FLoutRF pin is utilized as the RF Fastlock output pin. The value programmed into the RF_TOC[13:0] word represents two times the number of phase detector comparison cycles the RF synthesizer will spend in the Fastlock state.

RF_TOC	Fastlock Mode	Fastlock Period [CP events]	FLoutRF Pin Functionality
0	Disabled	N/A	High Impedance
1	Manual	N/A	Logic "0" State.
			Forces all Fastlock conditions
2	Disabled	N/A	Logic "0" State
3	Disabled	N/A	Logic "1" State
4	Enabled	4X2 = 8	Fastlock
5	Enabled	5X2 = 10	Fastlock
	Enabled		Fastlock
16383	Enabled	16383X2 = 32766	Fastlock

2.7.2 RF_CPF -- RF PLL Fastlock Charge Pump Current

Specify the charge pump current for the Fastlock operation mode for the RF PLL. Note that the Fastlock charge pump current, steady state current, and CSR control are all interrelated.

RF_CPF	RF Charge Pump State	Typical RF Charge Pump Current at 3 Volts (µA)				
0	1X	95				
1	2X	190				
2	3X	285				
3	4X	380				
4	5X	475				
5	6X	570				
6	7X	665				
7	8X	760				
8	9X	855				
9	10X	950				
10	11X	1045				
11	12X	1140				
12	13X	1235				
13	14X	1330				
14	15X	1425				
15	16X	1520				

2.7.3 CSR[1:0] -- RF Cycle Slip Reduction

CSR controls the operation of the Cycle Slip Reduction Circuit. This circuit can be used to reduce the occurrence of phase detector cycle slips. Note that the Fastlock charge pump current, steady state current, and CSR control are all interrelated. Refer to section 1.8 for information on how to use this.

CSR	CSR State	Sample Rate Reduction Factor
0	Disabled	1
1	Enabled	1/2
2	Enabled	1/4
3	Enabled	1/16

2.8 R7 REGISTER

REGISTER	23	22	21	20	19	18	17	16	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
Data[19:0]							C3	C2	C1	C0														
R7	0	0	0	0	0	0	0	0	0	0	DIV4	0	1	0	0	0	IF_RST	RF_RST	IF_CPT	RF_CPT	1	1	1	1

2.8.1 DIV4 -- RF Digital Lock Detect Divide By 4

Because the digital lock detect function is based on a phase error, it becomes more difficult to detect a locked condition for larger comparison frequencies. When this bit is enabled, it subdivides the RF PLL comparison frequency (it does not apply to the IF comparison frequency) presented to the digital lock detect circuitry by 4. This enables this circuitry to work at higher comparison frequencies. It is recommended that this bit be enabled whenever the comparison frequency exceeds 20 MHz and RF digital lock detect is being used.

2.8.2 IF_RST -- IF PLL Counter Reset

When this bit is enabled, the IF PLL N and R counters are reset, and the charge pump is put in a Tri-State condition. This feature should be disabled for normal operation. Note that a counter reset is applied whenever the chip is powered up via software or CE pin.

IF_RST	IF PLL N and R Counters	IF PLL Charge Pump
0 (Default)	Normal Operation	Normal Operation
1	Counter Reset	Tri-State

2.8.3 RF_RST -- RF PLL Counter Reset

When this bit is enabled, the RF PLL N and R counters are reset and the charge pump is put in a Tri-State condition. This feature should be disabled for normal operation. This feature should be disabled for normal operation. Note that a counter reset is applied whenever the chip is powered up via software or CE pin.

RF_RST	RF PLL N and R Counters	RF PLL Charge Pump
0 (Default)	Normal Operation	Normal Operation
1	Counter Reset	Tri-State

2.8.4 RF_TRI -- RF Charge Pump Tri-State

When this bit is enabled, the RF PLL charge pump is put in a Tri-State condition, but the counters are not reset. This feature is typically disabled for normal operation.

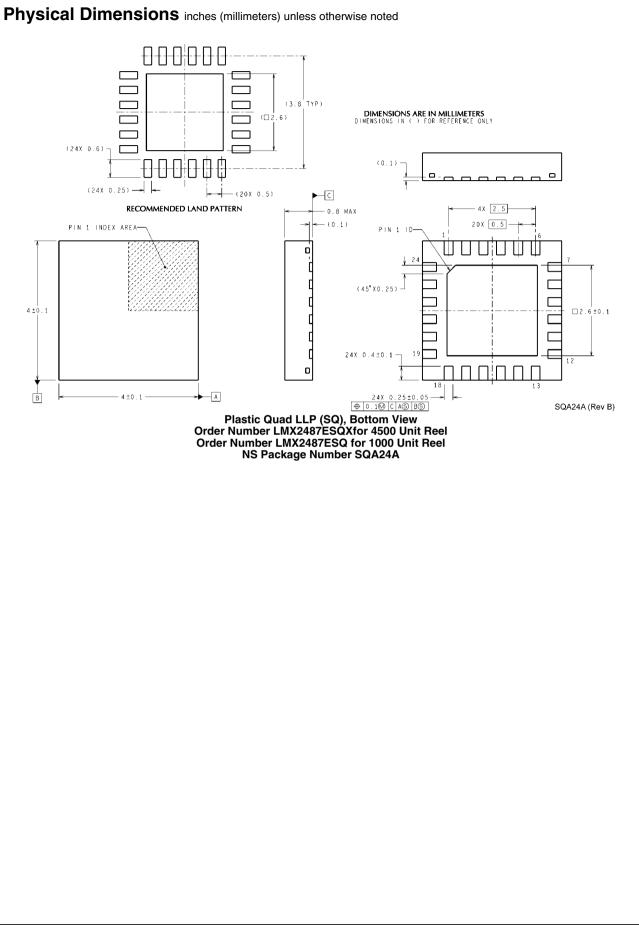
RF_TRI	RF PLL N and R Counters	RF PLL Charge Pump
0 (Default)	Normal Operation	Normal Operation
1	Normal Operation	Tri-State

2.8.5 IF_TRI -- IF Charge Pump Tri-State

When this bit is enabled, the IF PLL charge pump is put in a Tri-State condition, but the counters are not reset. This feature is typically disabled for normal operation.

IF_TRI	IF PLL N and R Counters	IF PLL Charge Pump
0 (Default)	Normal Operation	Normal Operation
1	Normal Operation	Tri-State





Notes

THE CONTENTS OF THIS DOCUMENT ARE PROVIDED IN CONNECTION WITH NATIONAL SEMICONDUCTOR CORPORATION ("NATIONAL") PRODUCTS. NATIONAL MAKES NO REPRESENTATIONS OR WARRANTIES WITH RESPECT TO THE ACCURACY OR COMPLETENESS OF THE CONTENTS OF THIS PUBLICATION AND RESERVES THE RIGHT TO MAKE CHANGES TO SPECIFICATIONS AND PRODUCT DESCRIPTIONS AT ANY TIME WITHOUT NOTICE. NO LICENSE, WHETHER EXPRESS, IMPLIED, ARISING BY ESTOPPEL OR OTHERWISE, TO ANY INTELLECTUAL PROPERTY RIGHTS IS GRANTED BY THIS DOCUMENT.

TESTING AND OTHER QUALITY CONTROLS ARE USED TO THE EXTENT NATIONAL DEEMS NECESSARY TO SUPPORT NATIONAL'S PRODUCT WARRANTY. EXCEPT WHERE MANDATED BY GOVERNMENT REQUIREMENTS, TESTING OF ALL PARAMETERS OF EACH PRODUCT IS NOT NECESSARILY PERFORMED. NATIONAL ASSUMES NO LIABILITY FOR APPLICATIONS ASSISTANCE OR BUYER PRODUCT DESIGN. BUYERS ARE RESPONSIBLE FOR THEIR PRODUCTS AND APPLICATIONS USING NATIONAL COMPONENTS. PRIOR TO USING OR DISTRIBUTING ANY PRODUCTS THAT INCLUDE NATIONAL COMPONENTS, BUYERS SHOULD PROVIDE ADEQUATE DESIGN, TESTING AND OPERATING SAFEGUARDS.

EXCEPT AS PROVIDED IN NATIONAL'S TERMS AND CONDITIONS OF SALE FOR SUCH PRODUCTS, NATIONAL ASSUMES NO LIABILITY WHATSOEVER, AND NATIONAL DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY RELATING TO THE SALE AND/OR USE OF NATIONAL PRODUCTS INCLUDING LIABILITY OR WARRANTIES RELATING TO FITNESS FOR A PARTICULAR PURPOSE, MERCHANTABILITY, OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

LIFE SUPPORT POLICY

NATIONAL'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS PRIOR WRITTEN APPROVAL OF THE CHIEF EXECUTIVE OFFICER AND GENERAL COUNSEL OF NATIONAL SEMICONDUCTOR CORPORATION. As used herein:

Life support devices or systems are devices which (a) are intended for surgical implant into the body, or (b) support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in a significant injury to the user. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system or to affect its safety or effectiveness.

National Semiconductor and the National Semiconductor logo are registered trademarks of National Semiconductor Corporation. All other brand or product names may be trademarks or registered trademarks of their respective holders.

Copyright© 2007 National Semiconductor Corporation

For the most current product information visit us at www.national.com



National Semiconductor Americas Customer Support Center Email: new.feedback@nsc.com Tel: 1-800-272-9959
 National Semiconductor Europe

 Customer Support Center

 Fax: +49 (0) 180-530-85-86

 Email: europe.support@nsc.com

 Deutsch Tel: +49 (0) 69 9508 6208

 English Tel: +49 (0) 87 024 0 2171

 Français Tel: +33 (0) 1 41 91 8790

National Semiconductor Asia Pacific Customer Support Center Email: ap.support@nsc.com National Semiconductor Japan Customer Support Center Fax: 81-3-5639-7507 Email: jpn.feedback@nsc.com Tel: 81-3-5639-7560